MAGX-000912-650L0x

GaN on SiC HEMT Pulsed Power Transistor
650 W Peak, 960-1215 MHz, 128 µs Pulse, 10% Duty

Rev. V2

Features

- GaN on SiC Depletion-Mode Transistor Technology
- Internally Matched
- Common-Source Configuration
- Broadband Class AB Operation
- 50 V Operation
- 800 W performance at 20µs and 6% duty factor
- RoHS* Compliant and 260°C Reflow Compatible
- MTTF = 600 years (T_J < 200°C)

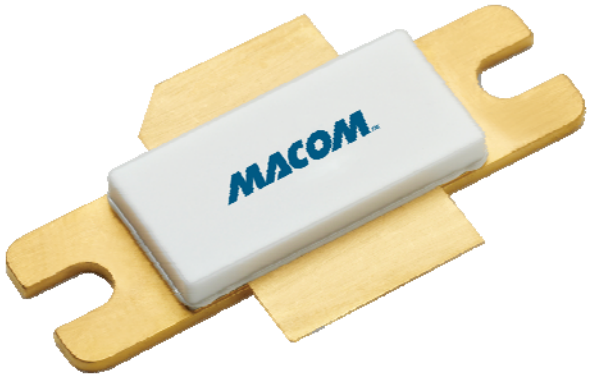
Applications

- L-Band pulsed radar.

Description

The MAGX-000912-650L00 and MAGX-000912-650L0S (MAGX-000912-650L0x) are gold metalized matched gallium nitride (GaN) on silicon carbide RF power transistor optimized for civilian and military pulsed avionics amplifier applications for the 960 MHz to 1215 MHz range such as Mode-S, TCAS, JTIDS, DME and TACAN. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.

MAGX-000912-650L00



MAGX-000912-650L0S

Ordering Information

Part Number	Description
MAGX-000912-650L00	Standard Flange
MAGX-000912-650L0S	Earless Flange
MAGX-A00912-650L00	960 - 1215 MHz Evaluation Board

1. When ordering the evaluation board, please indicate on sales order notes if it will be used for:
   A. Standard Flange devices
   B. Earless Flange devices

* Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

GaN on SiC HEMT Pulsed Power Transistor
650 W Peak, 960-1215 MHz, 128 µs Pulse, 10% Duty

Rev. V2

Typical RF Performance: (under standard operating conditions), P_{OUT} = 650 W (Peak)

Freq (MHz)	P_{IN} (W)	Gain (dB)	I_D (A)	Eff. (%)	RL (dB)	Droop (dB)	+1dB OD (W)	VSWR-S (3:1)	VSWR-T (3:1)
960	6.5	20	21	62	-8	0.3	740	S	P
1030	5.2	21	20.3	64	-13	0.2	723	S	P
1090	5.8	20.5	20.3	64	-11	0.3	719	S	P
1150	5.7	20.6	21	62	-15	0.3	720	S	P
1215	6.0	20.4	21.6	60	-11	0.2	718	S	P

Electrical Specifications: Freq. = 960 - 1215 MHz, T_A = 25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
RF Functional Tests: V_{DD} = 50 V; I_{DQ} = 500 mA; Pulse = 128 µs / 10%						
Input Power	P_{OUT} = 650 W Peak (65 W avg.)	P_{IN}	-	5.8	9.2	Wpk
Power Gain	P_{OUT} = 650 W Peak (65 W avg.)	G_P	18.5	20.5	-	dB
Drain Efficiency	P_{OUT} = 650 W Peak (65 W avg.)	η_D	57	62	-	%
Pulse Droop	P_{OUT} = 650 W Peak (65 W avg.)	Droop	-	0.3	0.5	dB
Load Mismatch Stability	P_{OUT} = 650 W Peak (65 W avg.)	VSWR-S	-	3:1	-	-
Load Mismatch Tolerance	P_{OUT} = 650 W Peak (65 W avg.)	VSWR-T	-	3:1	-	-

Electrical Characteristics: T_A = 25°C

Parameter	Test Conditions	Symbol	Typ.	Units
DC Characteristics				
Drain-Source Leakage Current	V_{GS} = -8 V, V_{DS} = 175 V	I_{DS}	1.7	mA
Gate Threshold Voltage	V_{DS} = 5 V, I_D = 90 mA	$V_{GS\ (TH)}$	-3.1	V
Forward Transconductance	V_{DS} = 5 V, I_D = 21 mA	G_M	22	S
Dynamic Characteristics				
Input Capacitance	Not applicable - Input matched	C_{ISS}	N/A	pF
Output Capacitance	V_{DS} = 50 V, V_{GS} = -8 V, F = 1 MHz	C_{OSS}	55	pF
Reverse Transfer Capacitance	V_{DS} = 50 V, V_{GS} = -8 V, F = 1 MHz	C_{RSS}	5.5	pF

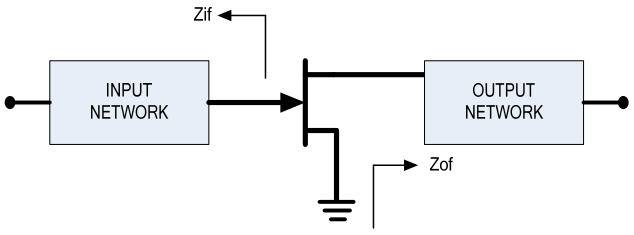
Absolute Maximum Ratings[2,3,4,5]

Parameter	Rating
Supply Voltage (V_{DD})	+65 V
Supply Voltage (V_{GS})	-8 to -2 V
Supply Current (I_D)	33 A
Input Power (P_{IN})	P_{IN} (nominal) +3 dB
Junction/Channel Temp	200°C
Pulsed Power Dissipation at +85°C	1 kW
Thermal Resistance, (T_J = +70°C) V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = 650 W, 128 µs Pulse / 10% Duty	0.17°C/W
Operating Temperature	-40 to +95°C
Storage Temperature	-65 to +150°C
Mounting Temperature	See solder reflow profile
ESD Min. - Charged Device Model (CDM)	1300 V
ESD Min. - Human Body Model (HBM)	4000 V

2. Operation of this device above any one of these parameters may cause permanent damage.
3. Input Power Limit is +3 dB over nominal drive required to achieve P_{OUT} = 650 W.
4. Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.
5. For saturated performance it recommended that the sum of ($3*V_{DD}$ + abs(V_{GG})) <175 V.

Test Fixture Impedances

F (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
960	0.7 - j0.9	1.4 + j0.7
1030	0.7 - j0.5	1.7 + j0.6
1060	0.8 - j0.1	1.7 + j0.5
1150	0.9 + j0.1	1.6 + j0.3
1215	1.1 + j0.4	1.2 + j0.4



Correct Device Sequencing

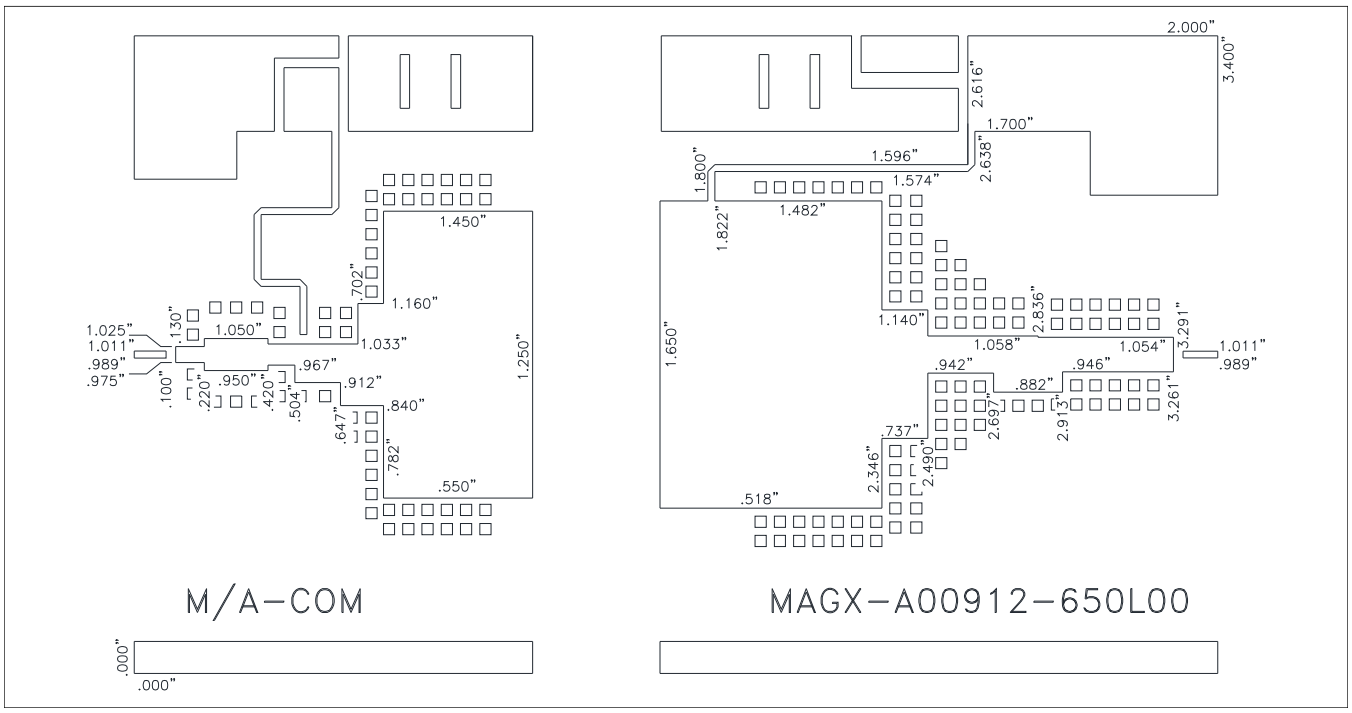
Turning the device ON

1. Set V_{GS} to the pinch-off (V_P), typically -5 V.
2. Turn on V_{DS} to nominal voltage (50 V).
3. Increase V_{GS} until the I_{DS} current is reached.
4. Apply RF power to desired level.

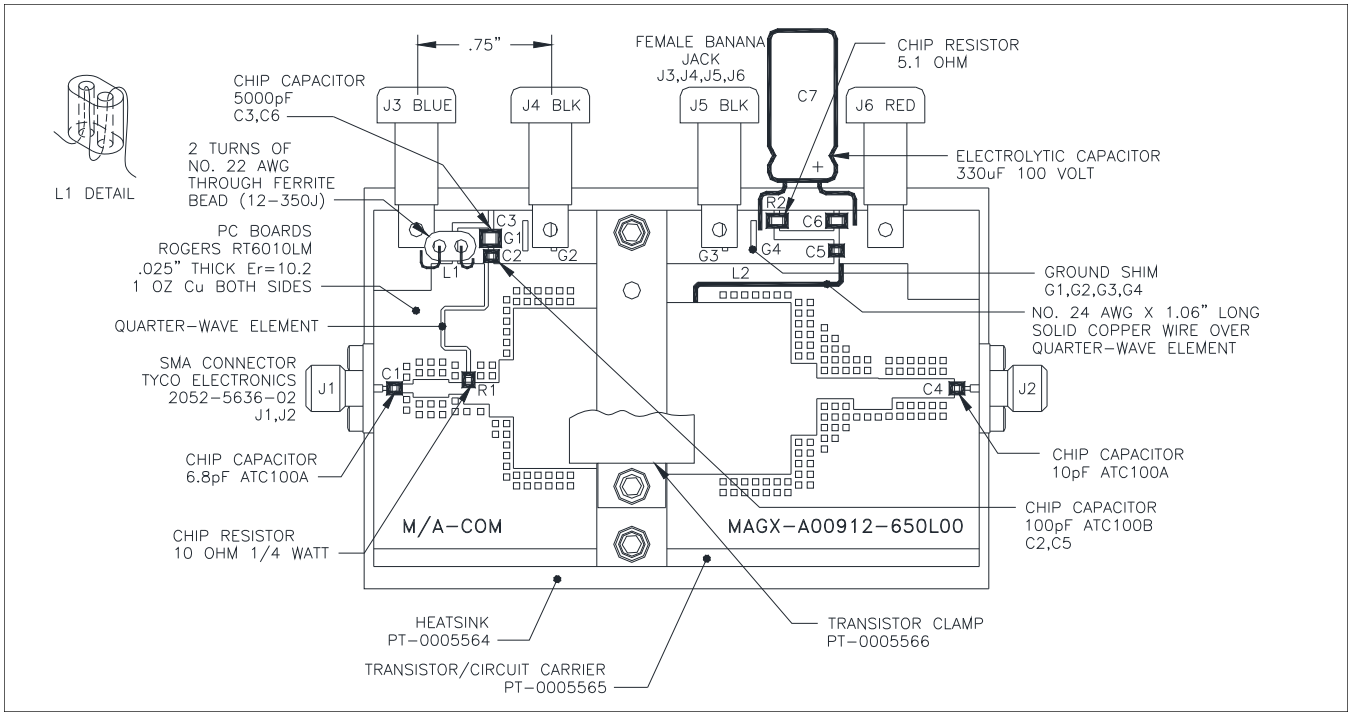
Turning the device OFF

1. Turn the RF power off.
2. Decrease V_{GS} down to V_P.
3. Decrease V_{DS} down to 0 V.
4. Turn off V_{GS}.

Test Fixture Circuit Dimensions

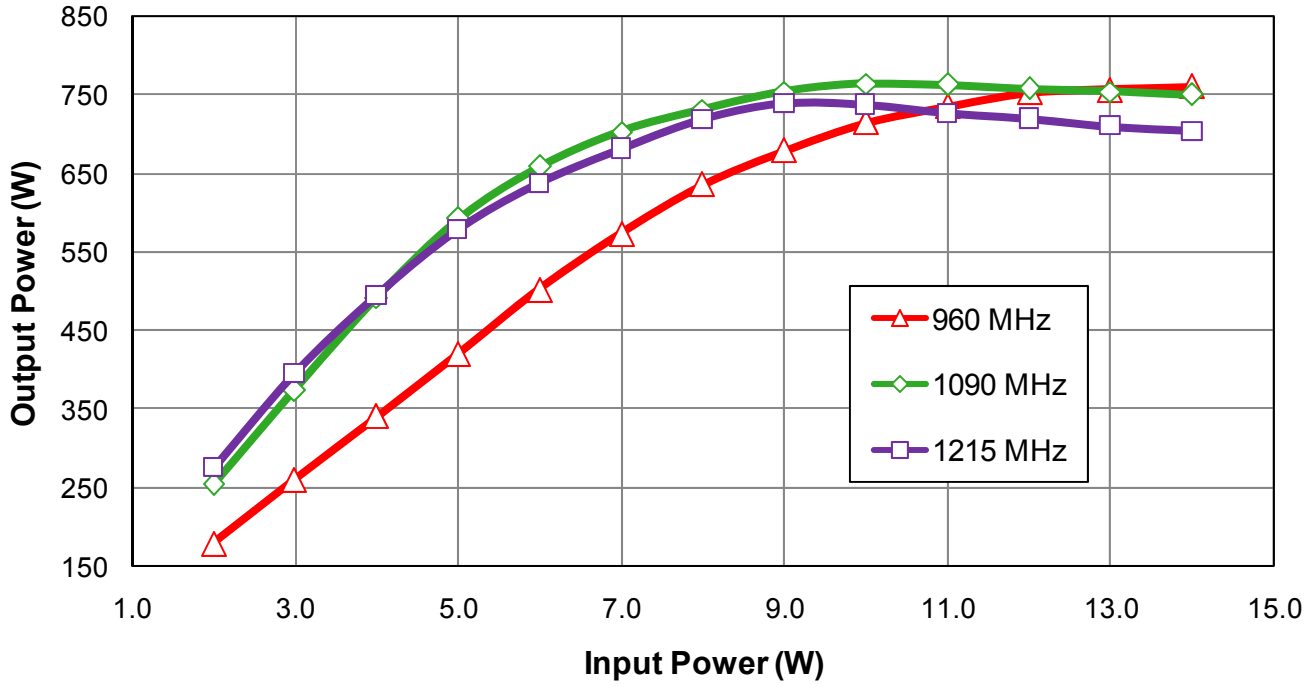


Test Fixture Assembly

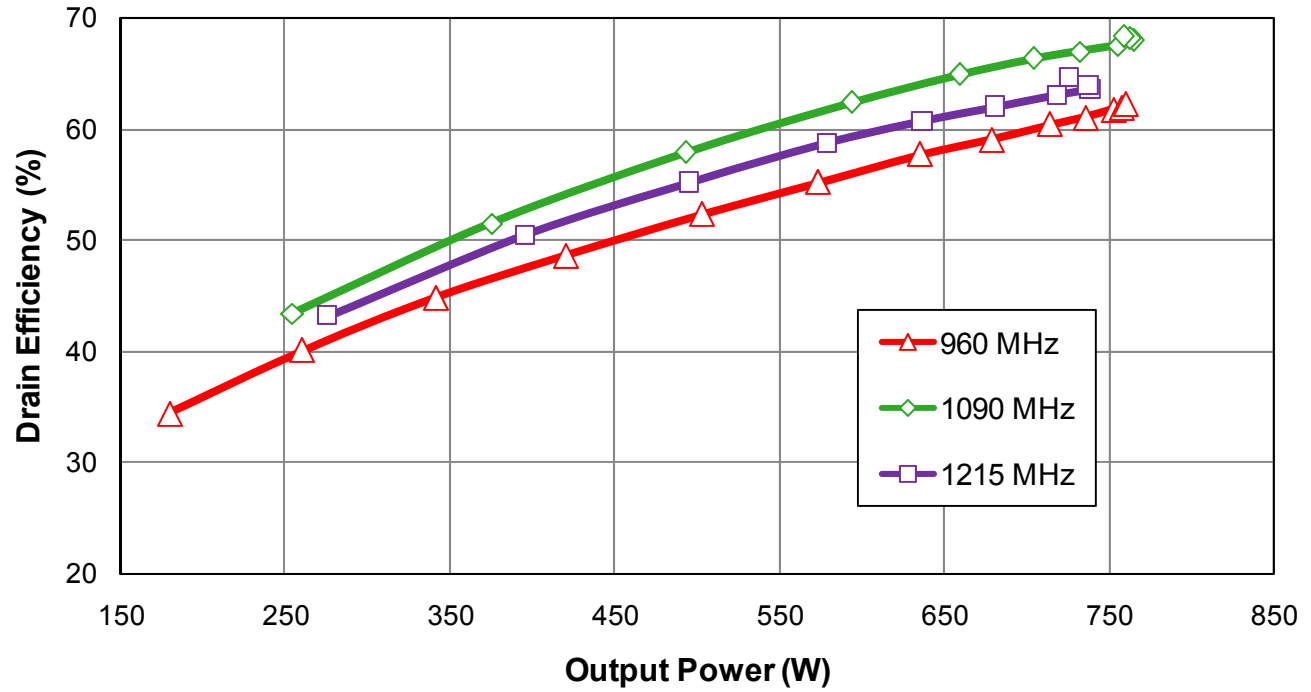


Contact factory for gerber file or additional circuit information.

RF Power Transfer Curve (Output Power vs. Input Power)



RF Power Transfer Curve (Drain Efficiency vs. Output Power)



Typical RF Performance under Alternate Operating Conditions[6,7]

V_{DD} = 55 V; I_{DQ} = 500 mA; Pulse = 20 µs / 6% , P_{OUT} = 800 W (Peak)

Freq (MHz)	P_{IN} (W)	Gain (dB)	I_D (A)	Eff. (%)	RL (dB)	Droop (dB)	+1dB OD (W)	VSWR-S (3:1)	VSWR-T (3:1)
1025	7.5	20.3	22.3	65.4	-11	0.1	875	S	P
1090	7.3	20.4	22.5	64.4	-11	0.1	872	S	P
1150	6.9	20.7	23.4	61.9	-14	0.1	875	S	P

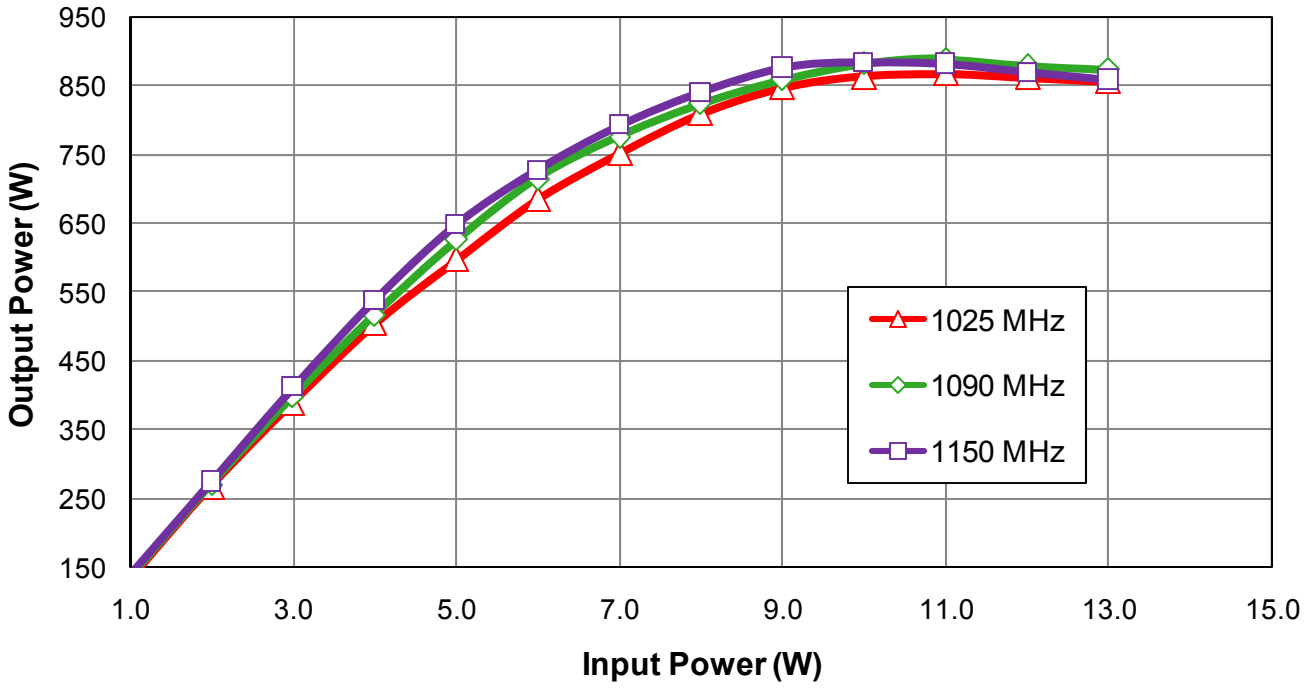
RF Performance (Alternate Operating Conditions[6,7]): Freq. = 1025 - 1150 MHz, T_A = 25°C

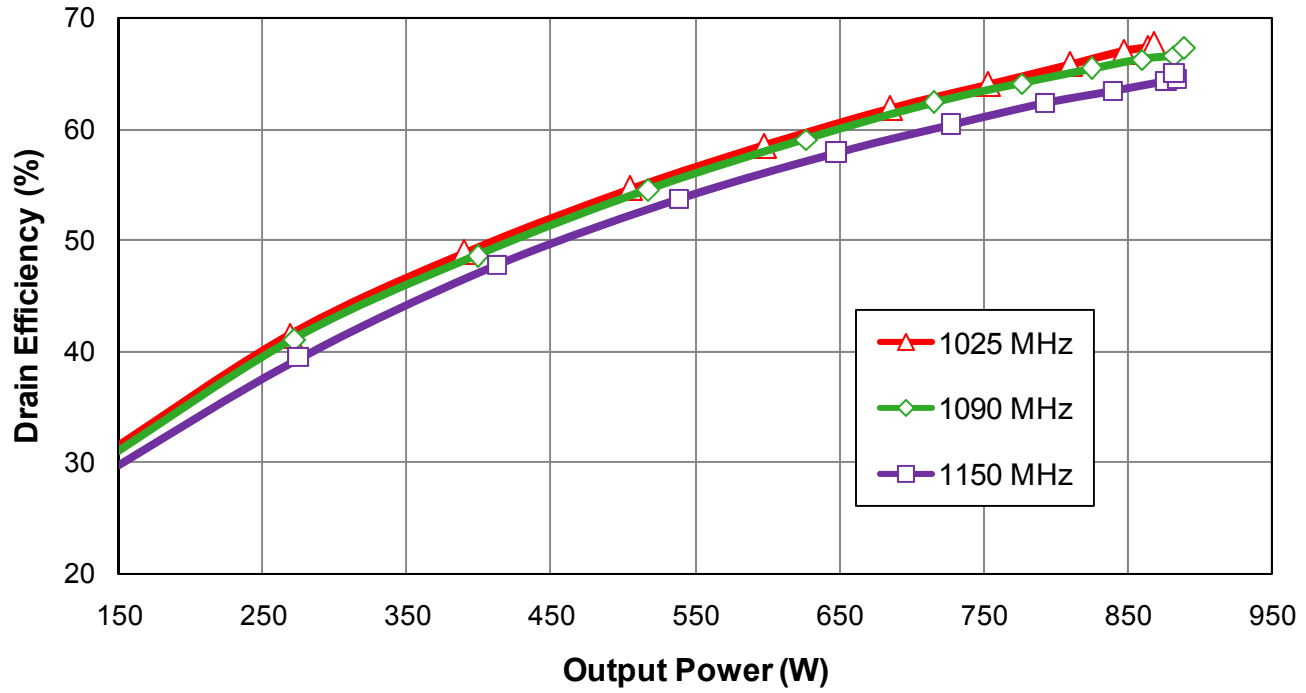
Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
RF Functional Tests: V_{DD} = 55 V; I_{DQ} = 500 mA; Pulse = 20 µs / 6%						
Input Power	P_{OUT} = 800 W Peak (48 W avg.)	P_{IN}	-	7.2	-	Wpk
Power Gain	P_{OUT} = 800 W Peak (48 W avg.)	G_P	-	20.4	-	dB
Drain Efficiency	P_{OUT} = 800 W Peak (48 W avg.)	η_D	-	63	-	%
Pulse Droop	P_{OUT} = 800 W Peak (48 W avg.)	Droop	-	0.1	-	dB
Load Mismatch Stability	P_{OUT} = 800 W Peak (48 W avg.)	VSWR-S	-	3:1	-	-
Load Mismatch Tolerance	P_{OUT} = 800 W Peak (48 W avg.)	VSWR-T	-	3:1	-	-

6. Operation of this device above V_{DD} = 50V may decrease operational lifetime.
7. Data measured in standard RF test fixture, reference page 4.

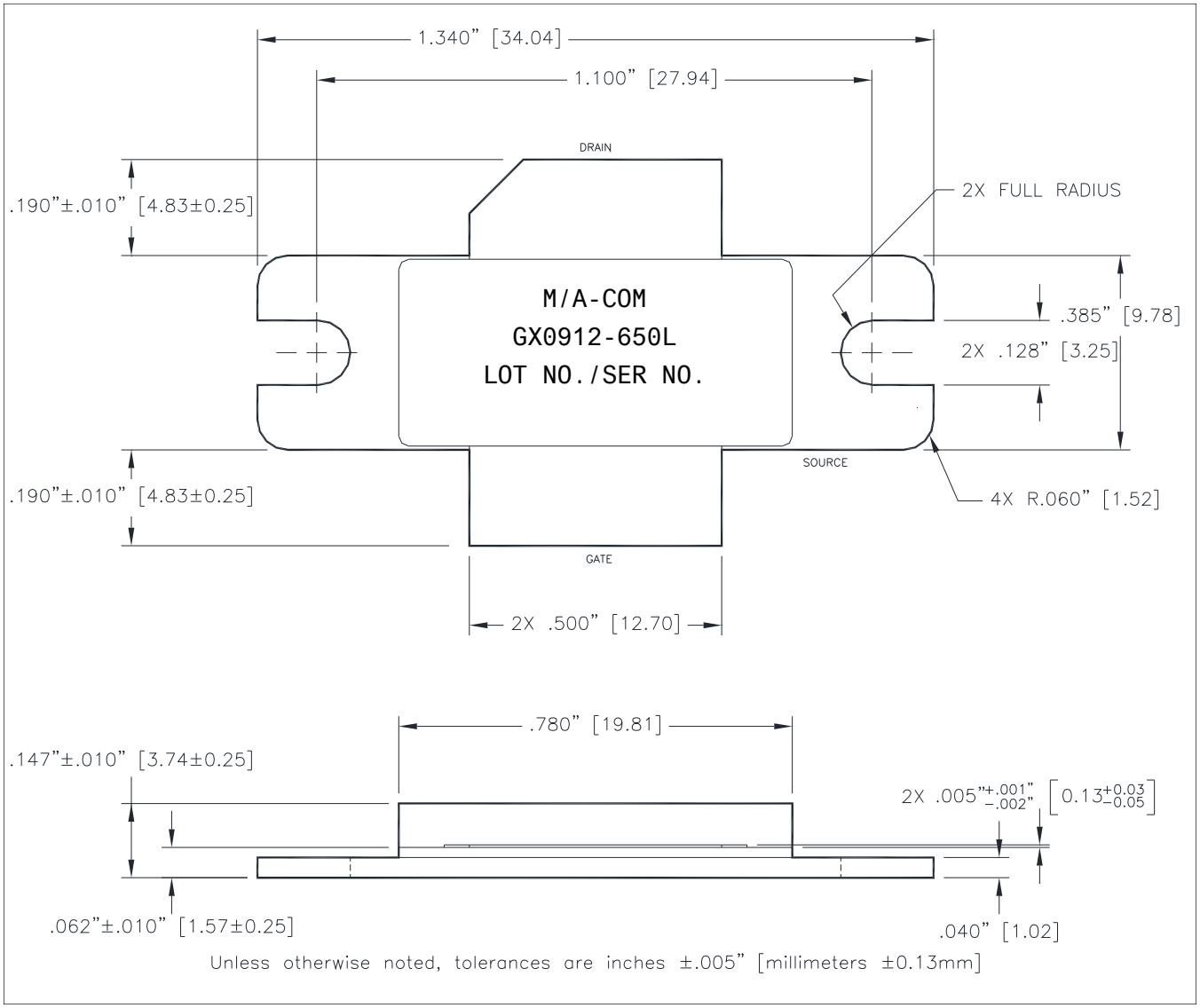
RF Power Transfer Curves under Alternate Operating Conditions[6,7]

(V_{DD} = 55 V; I_{DQ} = 500 mA; Pulse = 20 µs / 6%)

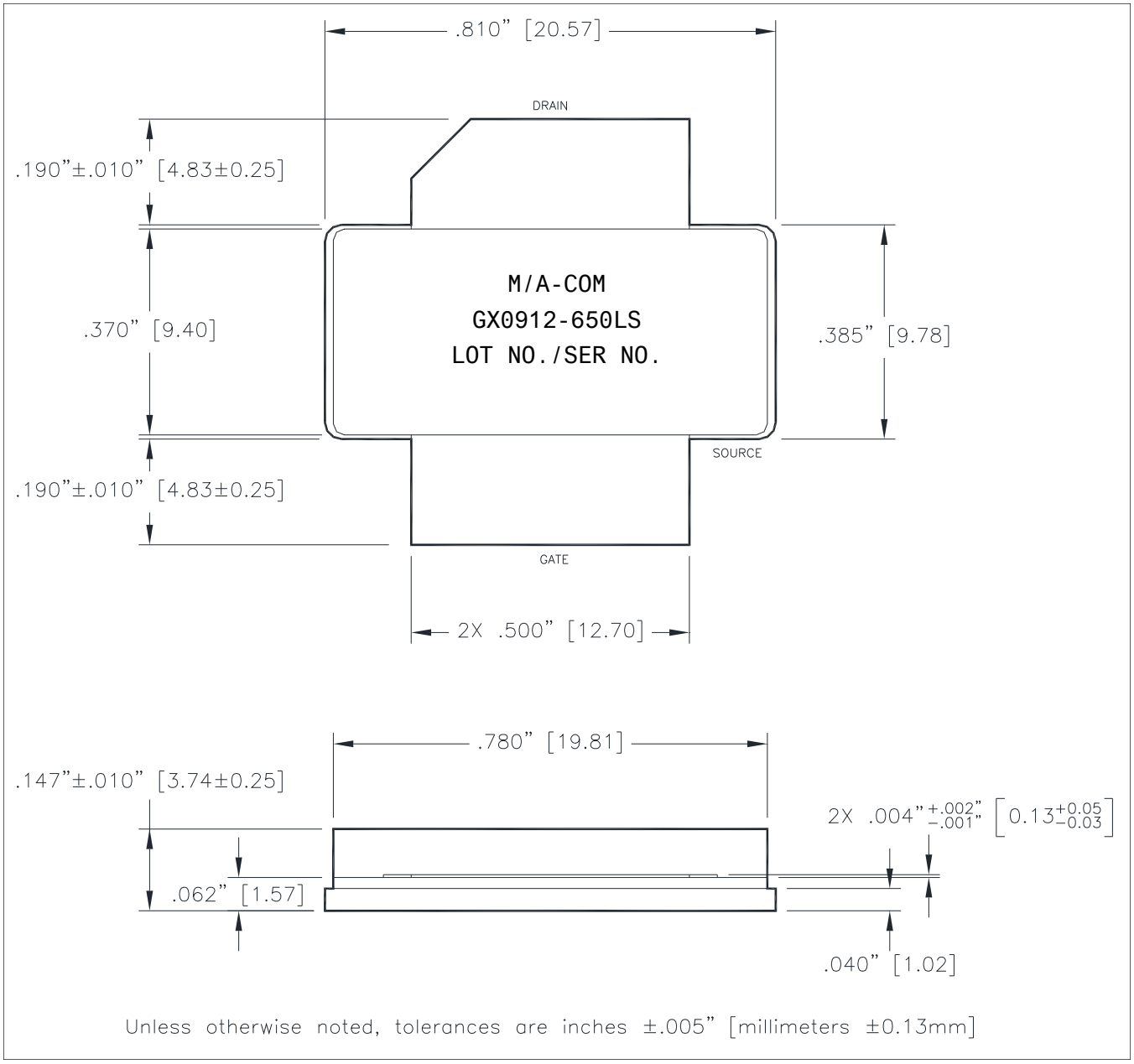




Outline Drawing MAGX-000912-650L00



Outline Drawing MAGX-000912-650L0S



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